

# NP180N04TUK

# MOS FIELD EFFECT TRANSISTOR

R07DS0542EJ0100 Rev.1.00 Sep 23, 2011

## **Description**

The NP180N04TUK is N-channel MOS Field Effect Transistor designed for high current switching applications.

#### **Features**

• Super low on-state resistance

 $R_{DS(on)} = 1.05 \text{ m}\Omega \text{ MAX.} (V_{GS} = 10 \text{ V}, I_D = 90 \text{ A})$ 

- Low  $C_{iss}$ :  $C_{iss} = 10500 \text{ pF TYP.}$  ( $V_{DS} = 25 \text{ V}$ )
- Designed for automotive application and AEC-Q101 qualified

#### **Ordering Information**

Part No.	Lead Plating	Pac	Package	
NP180N04TUK-E1-AY *1	Pure Sn (Tin)	Tape 800 p/reel	Taping (E1 type)	TO-263-7pin (MP-25ZT)
NP180N04TUK-E2-AY *1			Taping (E2 type)	

Note: \*1. Pb-free (This product does not contain Pb in the external electrode.)

## Absolute Maximum Ratings $(T_A = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V <sub>GS</sub> = 0 V)	V <sub>DSS</sub>	40	V
Gate to Source Voltage (V <sub>DS</sub> = 0 V)	V <sub>GSS</sub>	±20	V
Drain Current (DC) (T <sub>C</sub> = 25°C)	I <sub>D(DC)</sub>	±180	Α
Drain Current (pulse) *1	I <sub>D(pulse)</sub>	±720	А
Total Power Dissipation (T <sub>C</sub> = 25°C)	P <sub>T1</sub>	348	W
Total Power Dissipation (T <sub>A</sub> = 25°C)	P <sub>T2</sub>	1.8	W
Channel Temperature	T <sub>ch</sub>	175	°C
Storage Temperature	T <sub>stg</sub>	−55 to +175	°C
Repetitive Avalanche Current *2	I <sub>AR</sub>	72	A
Repetitive Avalanche Energy *2	E <sub>AR</sub>	518	mJ

## **Thermal Resistance**

Notes: \*1.  $T_C$  = 25°C, PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

\*2.  $R_G = 25 \Omega$ ,  $V_{GS} = 20 \rightarrow 0 V$ 

# Electrical Characteristics (T<sub>A</sub> = 25°C)

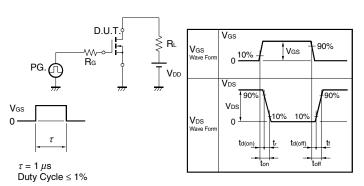
Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			1	μΑ	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V
Gate Leakage Current	I <sub>GSS</sub>			±100	nA	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate to Source Threshold Voltage	$V_{GS(th)}$	2.0	3.0	4.0	<b>&gt;</b>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Forward Transfer Admittance *1	y <sub>fs</sub>	75	150		S	$V_{DS} = 5 \text{ V}, I_{D} = 90 \text{ A}$
Drain to Source On-state Resistance *1	R <sub>DS(on)</sub>		0.85	1.05	mΩ	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 90 A
Input Capacitance	C <sub>iss</sub>		10500	15750	pF	V <sub>DS</sub> = 25 V,
Output Capacitance	Coss		1600	2400	pF	V <sub>GS</sub> = 0 V,
Reverse Transfer Capacitance	C <sub>rss</sub>		540	980	pF	f = 1 MHz
Turn-on Delay Time	$t_{d(on)}$		38	90	ns	$V_{DD} = 20 \text{ V}, I_D = 90 \text{ A},$
Rise Time	t <sub>r</sub>		22	60	ns	V <sub>GS</sub> = 10 V,
Turn-off Delay Time	t <sub>d(off)</sub>		140	280	ns	$R_G = 0 \Omega$
Fall Time	t <sub>f</sub>		20	50	ns	
Total Gate Charge	$Q_G$		198	297	nC	V <sub>DD</sub> = 32 V,
Gate to Source Charge	Q <sub>GS</sub>		50		nC	V <sub>GS</sub> = 10 V,
Gate to Drain Charge	$Q_{GD}$		48		nC	I <sub>D</sub> = 180 A
Body Diode Forward Voltage *1	$V_{F(S-D)}$		0.9	1.5	V	I <sub>F</sub> = 180 A, V <sub>GS</sub> = 0 V
Reverse Recovery Time	t <sub>rr</sub>		83		ns	I <sub>F</sub> = 180 A, V <sub>GS</sub> = 0 V,
Reverse Recovery Charge	Q <sub>rr</sub>		130		nC	di/dt = 100 A/μs

Note: \*1. Pulsed test

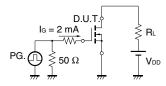
#### **TEST CIRCUIT 1 AVALANCHE CAPABILITY**

# $PG. \bigcirc PG. \bigcirc PG.$

#### **TEST CIRCUIT 2 SWITCHING TIME**



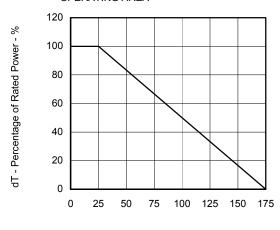
#### **TEST CIRCUIT 3 GATE CHARGE**



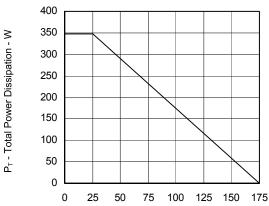
I<sub>D</sub> - Drain Current - A

## Typical Characteristics ( $T_A = 25^{\circ}C$ )

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



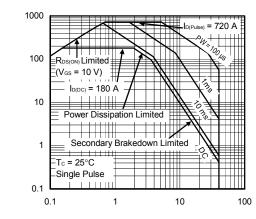
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



T<sub>C</sub> - Case Temperature - °C

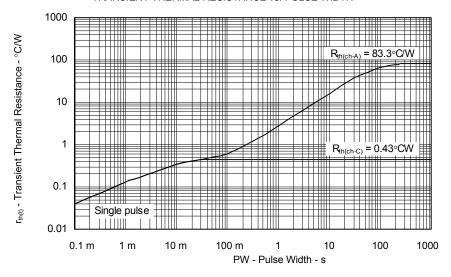
#### $T_{\text{C}}$ - Case Temperature - $^{\circ}\text{C}$

#### FORWARD BIAS SAFE OPERATING AREA

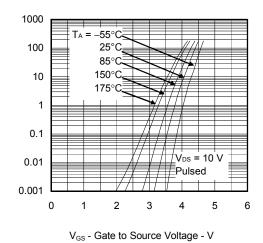


V<sub>DS</sub> - Drain to Source Voltage - V

#### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



#### DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE 800 700 600 I<sub>D</sub> - Drain Current - A 500 400 300 200 V<sub>GS</sub> = 10 V Pulsed 100 0 0.2 0 0.4 0.6 8.0 V<sub>DS</sub> - Drain to Source Voltage - V



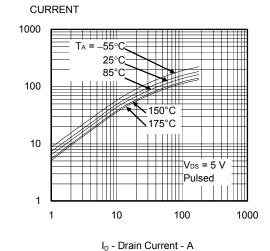
FORWARD TRANSFER CHARACTERISTICS

y<sub>fs</sub> | - Forward Transfer Admittance - S

I<sub>D</sub> - Drain Current - A

vs. CHANNEL TEMPERATURE V<sub>GS(th)</sub> - Gate to Source Threshold Voltage - V VDS = VGS I<sub>D</sub> = 250 μA 3 2 0 -100 -50 0 50 100 150 200

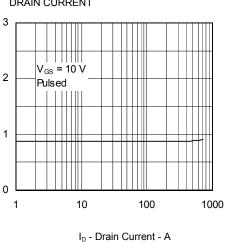
GATE TO SOURCE THRESHOLD VOLTAGE

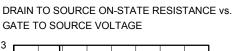


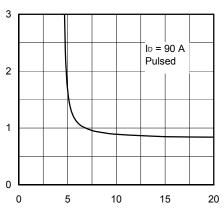
FORWARD TRANSFER ADMITTANCE vs. DRAIN



 $T_{\text{ch}}$  - Channel Temperature -  $^{\circ}C$ 







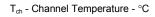
V<sub>GS</sub> - Gate to Source Voltage - V

 $R_{\text{DS}(\text{on})}$  - Drain to Source On-state Resistance -  $m\Omega$ 

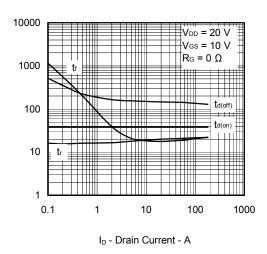
R<sub>DS(on)</sub> - Drain to Source On-state Resistance - mΩ

 $R_{DS(on)}$  - Drain to Source On-state Resistance -  $m\Omega$ 

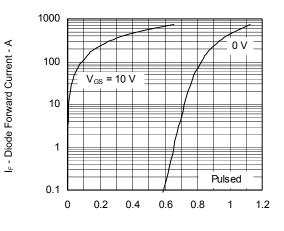
t<sub>d(on)</sub>, tr, t<sub>d(off)</sub>, tr - Switching Time - ns



#### SWITCHING CHARACTERISTICS

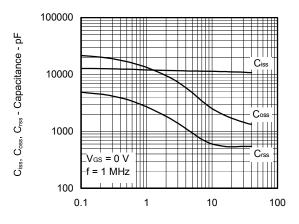


#### SOURCE TO DRAIN DIODE FORWARD VOLTAGE



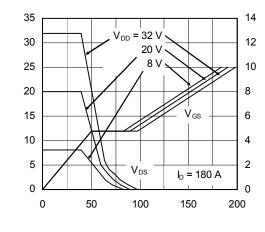
 $V_{\text{F(S-D)}}$  - Source to Drain Voltage - V

#### CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



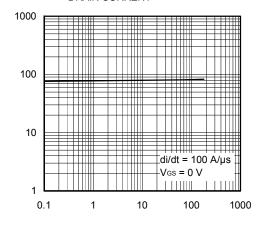
V<sub>DS</sub> - Drain to Source Voltage - V

#### DYNAMIC INPUT/OUTPUT CHARACTERISTICS



 $\ensuremath{\mathsf{Q}}_{\ensuremath{\mathsf{G}}}$  - Gate Charge - nC

# REVERSE RECOVERY TIME vs. DRAIN CURRENT



I<sub>F</sub> - Drain Current - A

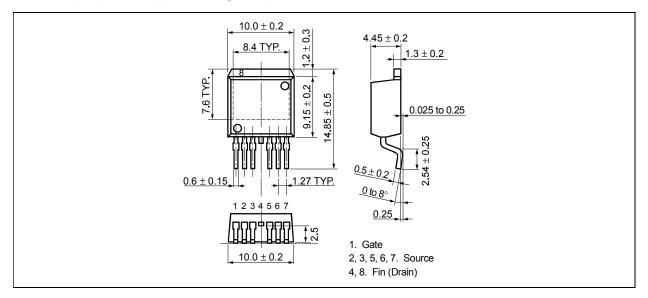
z

V<sub>DS</sub> - Drain to Source Voltage - V

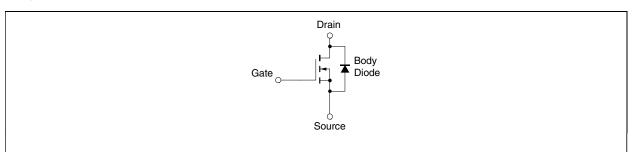
t<sub>rr</sub> - Reverse Recovery Time - ns

## Package Drawing (Unit: mm)

## TO-263-7pin (MP-25ZT) (Mass: 1.5 g TYP.)



## **Equivalent Circuit**



**Remark** Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

# NP180N04TUK Data Sheet

		Description		
Rev.	Date	Page	Summary	
1.00	Sep 23, 2011	-	First Edition Issued	

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